a substrate of a first conductive type;

a first doped region and a second doped region of a second conductive type formed in the substrate, the first and second doped regions being spaced apart enabling a channel region formed in between;

a well region of the second conductive type, formed in the substrate; and

a third doped region of the first conductive type disposed in the well region, and electrically floated in the well region so that the third doped region has no DC connection to the first node, wherein the first node is electrically coupled to the first doped region and the well region, and the second node is electrically coupled to the second doped region.

38. (Amended) An electrostatic discharge protection circuit coupled between a first node and a second node, comprising:

a substrate of a first conductive type;

a first doped region and a second doped region of a second conductive type formed in the substrate, the first and second doped regions being spaced apart enabling a channel region formed in between;

a well region of the second conductive type, formed in the substrate; and

a third doped region of the first conductive type disposed in the well region,

wherein the third doped region is coupled to the first node through a capacitor,

wherein the first node is electrically coupled to the first doped region and the well region, and the second node is electrically coupled to the second doped region.

Please add the following new claim:

39. (New) An output buffer, comprising:

a first circuit coupled between a first power line and a pad; and

a second circuit coupled between a second power line and the pad, comprising:

a resistor constructed by a well region of a second conductivity type deposited on a substrate of a first conductivity type, the resistor comprising a first end and a second end, the first end being a doped region of the second conductivity type at least partially overlapping the well region and coupled to the pad;

a first doped region of the first conductivity type deposited in the well region, wherein the first doped region is at least capacitively coupled to the pad and electrically floated in the well in that there is no DC connection between the first doped region and the pad; and

an electrostatic discharge protection component coupled between the second end and the second power line.